

**2SK1412**

N-Channel MOS Silicon FET

High-Voltage High-Speed
Switching Applications**Features**

- Low ON resistance, low input capacitance, very high-speed switching.
- High reliability (Adoption of HVP process).
- Micaless package facilitating mounting.

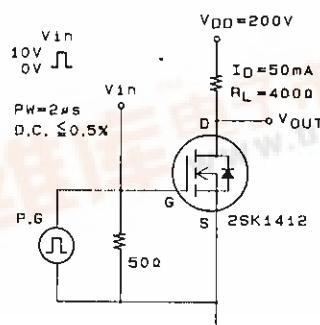
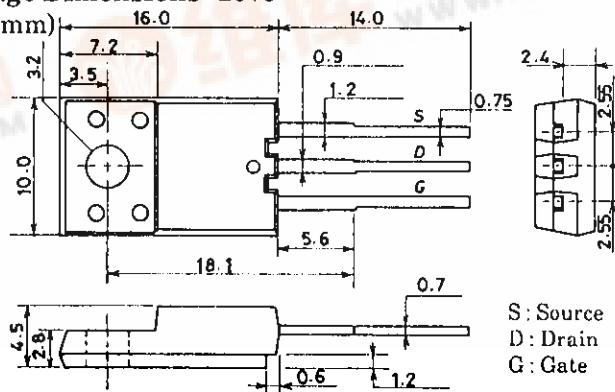
Absolute Maximum Ratings at Ta = 25°C

		unit
Drain to Source Voltage	V _{DSS}	1500 V
Gate to Source Voltage	V _{GSS}	±20 V
Drain Current(DC)	I _D	0.1 A
Drain Current(Pulse)	I _{DP}	PW≤10μs, duty cycle≤1% 0.2 A
Allowable Power Dissipation	P _D	2.0 W
		T _c =25°C 20 W
Channel Temperature	T _{ch}	150 °C
Storage Temperature	T _{stg}	-55 to +150 °C

Electrical Characteristics at Ta = 25°C

		min	typ	max	unit
D-S Breakdown Voltage	V _{(BR)DSS}	1500			V
Zero Gate Voltage	I _{DSS}			100	μA
Drain Current					
Gate to Source Leakage Current	I _{GSS}			±100	nA
Cutoff Voltage	V _{GS(off)}			3.5	V
Forward Transfer Admittance	Y _{fs}			50	mS
Static Drain to Source	R _{DSS(on)}			140	Ω
on State Resistance				200	
Input Capacitance	C _{iss}			40	pF
Output Capacitance	C _{oss}			12	pF
Reverse Transfer Capacitance	C _{rss}			3.0	pF
Turn-ON Delay Time	t _{d(on)}			15	ns
Rise Time	t _r			25	ns
Turn-OFF Delay Time	t _{d(off)}			50	ns
Fall Time	t _f			350	ns
Diode Forward Voltage	V _{SD}			1.0	1.5
		I _S =0.1A, V _{GS} =0			V

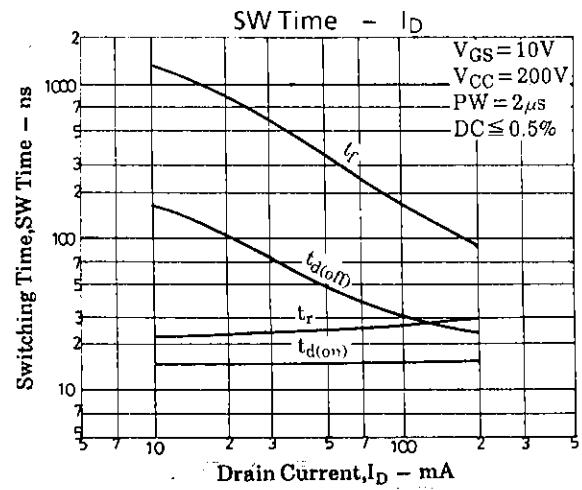
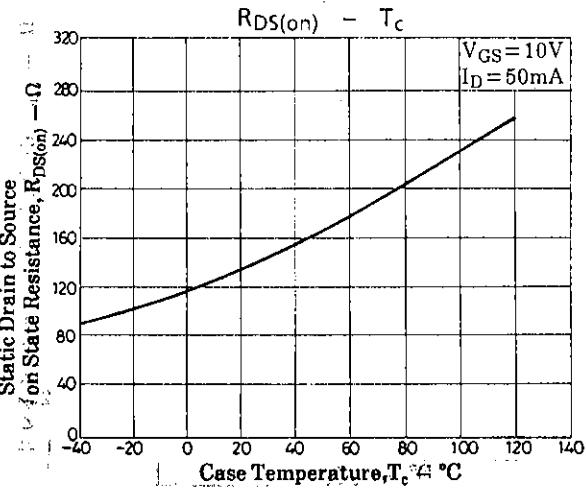
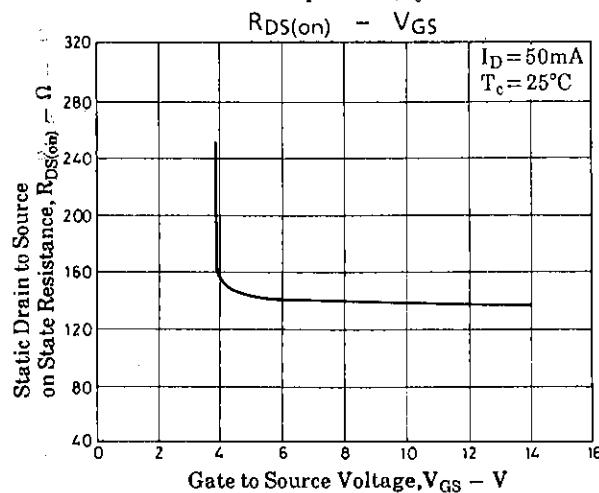
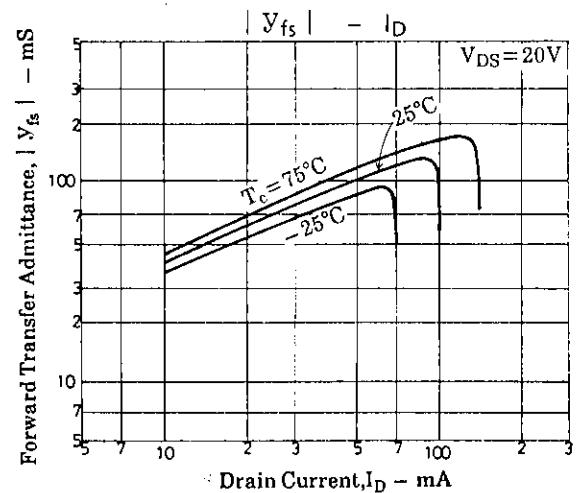
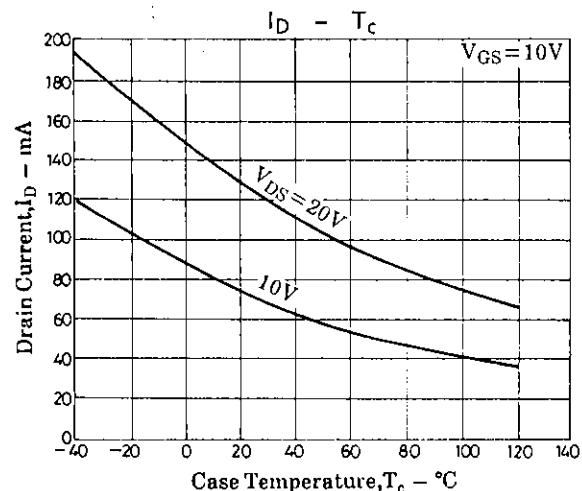
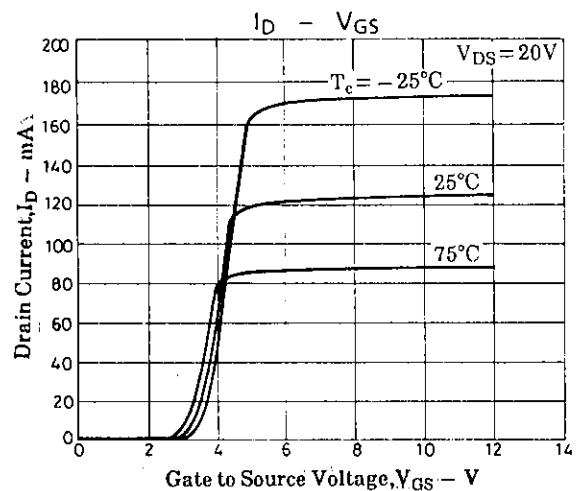
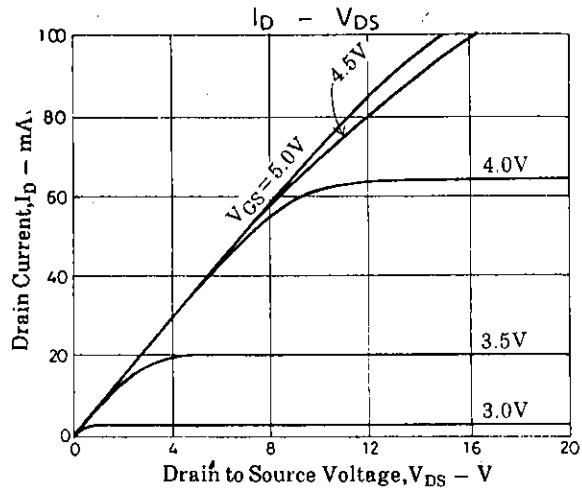
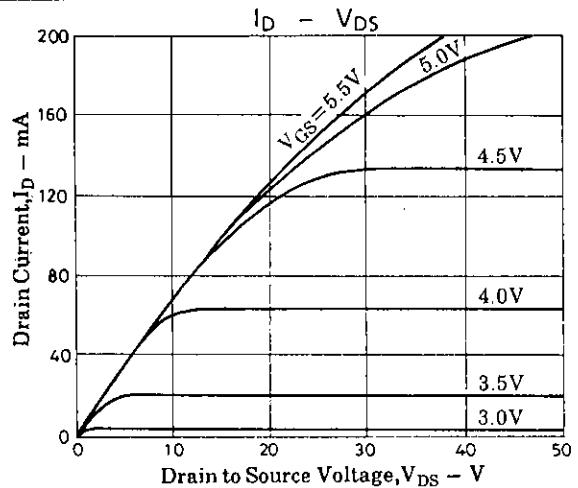
(Note) Be careful in handling the 2SK1412 because it has no protection diode between gate and source.

Switching Time Test Circuit**Package Dimensions 2078**

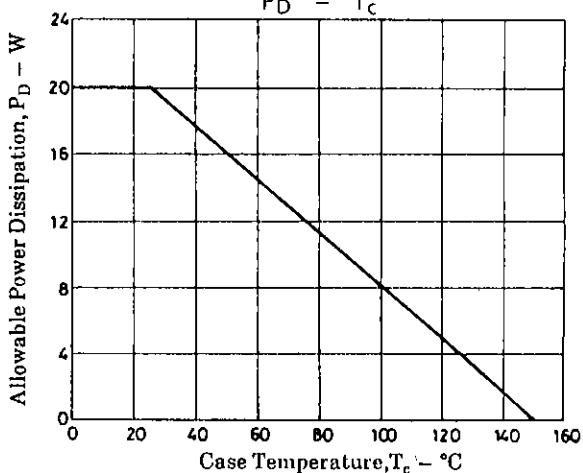
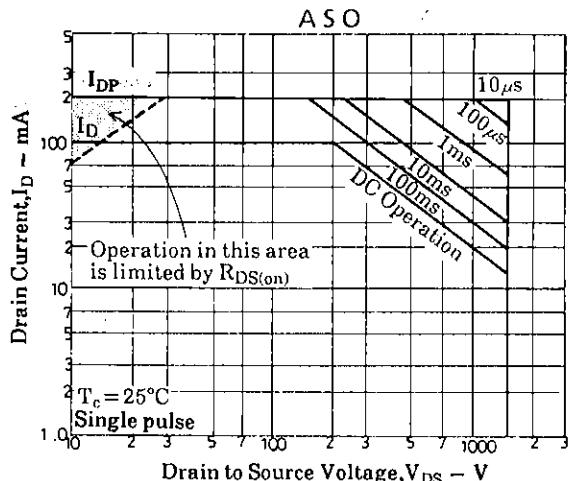
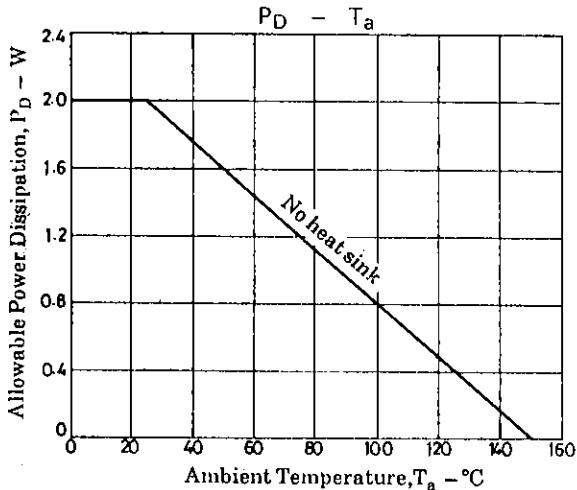
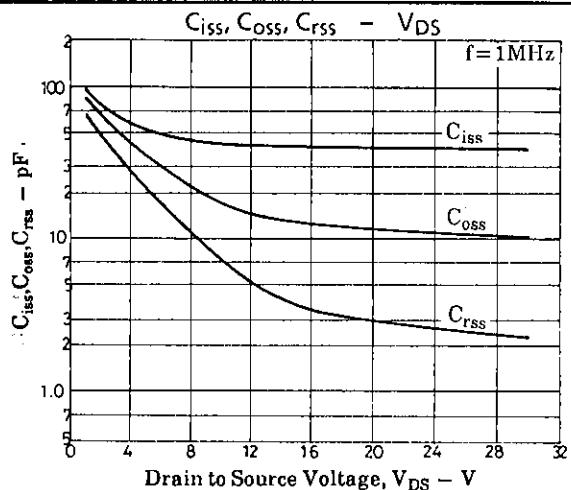
S : Source
D : Drain
G : Gate

SANYO : TO-220FI

2SK1412



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